

**Amendments to the Written Description of the Specification**

Applicant presents replacement paragraphs below indicating the changes with insertions indicated by underlining and deletions indicated by strikeouts and/or double bracketing.

Please amend the last paragraph on page 4, lines 19-26 as shown below:

--One particular refinement of the invention is characterized by opening of the ASIC passivation in the photoactive region of the TFA sensor, removal of the antireflection layer of the upper metalization layer of the ASIC in the photoactive region of the TFA sensor, removal of the conductive layer of the upper ~~metalization~~ metallization layer of the ASIC in the photoactive region of the TFA sensor, patterning or removal of the lower barrier layer of the upper ~~metalization~~ metallization layer of the ASIC in the photoactive region of the TFA sensor, deposition and patterning of a further metal layer, deposition and patterning of the photodiode layers, and deposition and patterning of further layers, such as color filter layers.--

On page 8, after line 23, please insert:

--Such alterations, modifications, and improvements are intended to be part of this disclosure, and are intended to be within the spirit and the scope of the present invention. Accordingly, the foregoing description is by way of example only and is not intended to be limiting. The present invention is limited only as defined in the following claims and the equivalents thereto.

What is claimed is:--